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ABSTRACT:

“A Method of Fabricating Semiconductor Structures and a Semiconductor Structure Formed Thereby”

A method of fabricating a silicide layer on a silicon region of a semiconductor structure, the method comprising the steps of: providing a semiconductor structure having at least one silicon region on a surface thereof; depositing a layer of nickel and platinum on the at least one silicon layer; annealing the semiconductor structure and the nickel/platinum layer to react the nickel and the platinum with underlying silicon to form a nickel-platinum silicide, wherein the annealing step takes place at temperature of between 680°C and 720°C.



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[FIGURE 1]